

NVMFS5A160PLZ

MOSFET – Power, Single P-Channel

-60 V, -100 A, 7.7 mΩ



ON Semiconductor®

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Features

- Small Footprint (5 x 6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- NVMFS5A160PLZWf: Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

SPECIFICATION MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (Notes 1, 2, 3)

Symbol	Parameter		Value	Unit	
V_{DSS}	Drain to Source Voltage		-60	V	
V_{GS}	Gate to Source Voltage		± 20	V	
I_D	Continuous Drain Current $R_{\theta JC}$, (Notes 1, 3)	Steady State	$T_C = 25^\circ\text{C}$	-100	A
P_D			Power Dissipation $R_{\theta JC}$ (Note 1)	$T_C = 25^\circ\text{C}$	200
I_D	Continuous Drain Current: $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	$T_A = 25^\circ\text{C}$	-15	A
P_D			Power Dissipation $R_{\theta JA}$ (Note 1, 2)	$T_A = 25^\circ\text{C}$	3.8
I_{DP}	Pulsed Drain Current	$PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$	-400	A	
T_J, T_{STG}	Operating Junction and Storage Temperature		-55 to +175	$^\circ\text{C}$	
I_S	Source Current (Body Diode)		-100	A	
E_{AS}	Single Pulse Drain to Source Avalanche Energy ($L = 1.0 \text{ mH}$, $I_{L(pk)} = -26 \text{ A}$)		335	mJ	
T_L	Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		260	$^\circ\text{C}$	

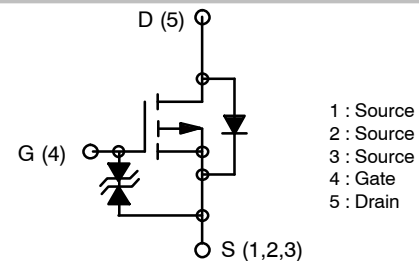
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

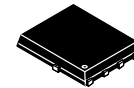
Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Junction to Case Steady State	0.75	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction to Ambient Steady State (Note 3)	39	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

V_{DSS}	$R_{DS(on)}$ MAX	I_D MAX
-60 V	7.7 mΩ @ -10 V	-100 A
	10.5 mΩ @ -4.5 V	

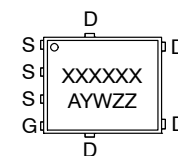


P-CHANNEL MOSFET



DFN5 (SO-8FL)

MARKING DIAGRAM



XXXXXX = Specific Device Code
 5A160L(NVMFS5A160PLZ)
 160LWF(NVMFS5A160PLZWf)
 A = Assembly Location
 Y = Year
 W = Work Week
 ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

NVMFS5A160PLZ

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

V _{(BR)DSS}	Drain to Source Breakdown Voltage	I _D = -1 mA, V _{GS} = 0 V	-60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -60 V, V _{GS} = 0 V	T _J = 25°C		-1.0	μA
			T _J = 100°C (Note 4)		-100	μA
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±16 V, V _{DS} = 0 V			±10	μA

ON CHARACTERISTICS (Note 5)

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = -10 V, I _D = -1 mA	-1.2		-2.6	V
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = -10 V	I _D = -50 A	5.8	7.7	mΩ
		V _{GS} = -4.5 V	I _D = -50 A	7.3	10.5	
g _{FS}	Forward Transconductance	V _{DS} = -10 V, I _D = -50 A		119		S

CHARGES, CAPACITANCES & GATE RESISTANCE

C _{iss}	Input Capacitance	V _{GS} = 0 V, f = 1 MHz V _{DS} = -20 V,			7700	pF
C _{oss}	Output Capacitance				720	
C _{rss}	Reverse Transfer Capacitance				540	
Q _{g(tot)}	Total Gate Charge	V _{GS} = -10 V, I _D = -50 A V _{DS} = -36 V,			160	nC
Q _{gs}	Gate to Source Charge				24	
Q _{gd}	Gate to Drain Charge				45	

SWITCHING CHARACTERISTICS (Note 6)

t _{d(on)}	Turn-On Delay Time	V _{DS} = -36 V, I _D = -50 A, V _{GS} = -10 V, R _G = 50 Ω			50	ns
t _r	Rise Time				690	
t _{d(off)}	Turn-Off Delay Time				645	
t _f	Fall Time				643	

DRAIN-SOURCE DIODE CHARACTERISTICS

V _{SD}	Forward Diode Voltage	V _{GS} = 0 V, I _S = -50 A			-0.83	-1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = -50 A			93		ns
Q _{rr}	Reverse Recovery Charge	di/dt = 100 A/μs			218		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The maximum value is specified by design at T_J = 100 °C. Product is not tested to this condition in production.

5. Pulse Test: pulse width ≤ 300μs, duty cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

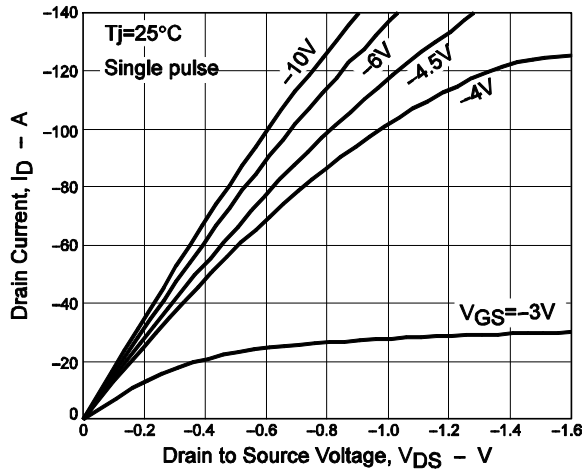


Figure 1. $I_D - V_{DS}$

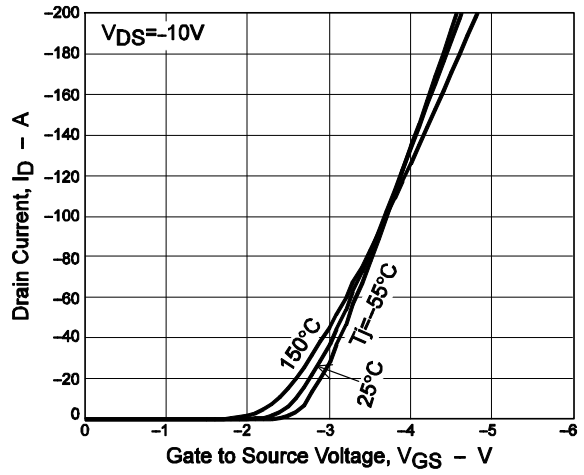


Figure 2. $I_D - V_{GS}$

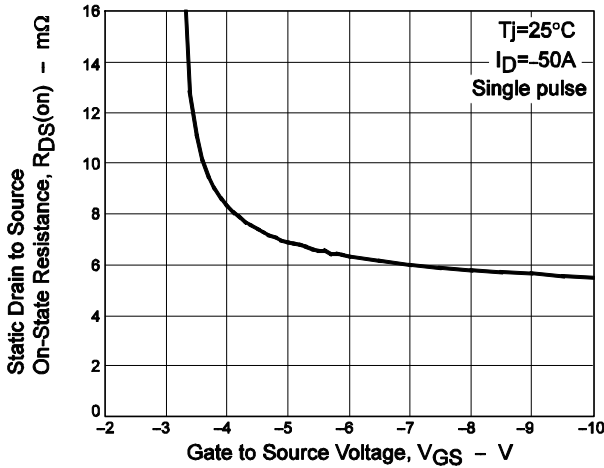


Figure 3. $R_{DS(on)} - V_{GS}$

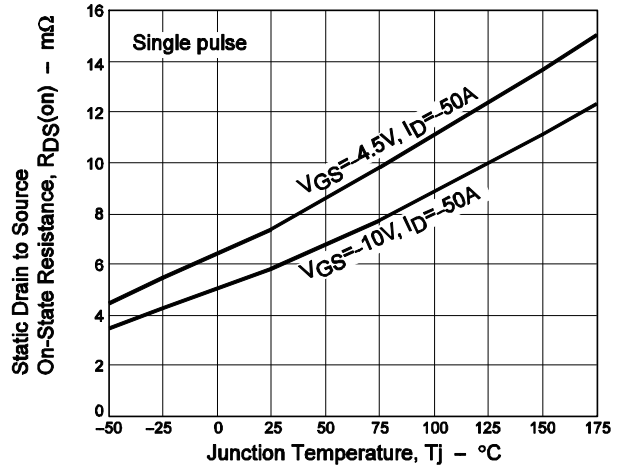


Figure 4. $R_{DS(on)} - T_J$

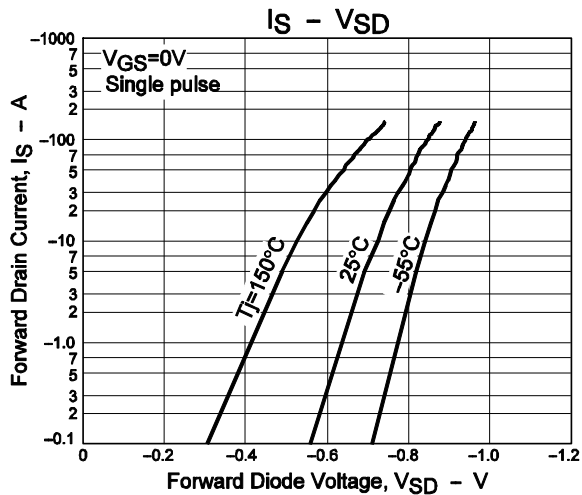


Figure 5. $I_S - V_{SD}$

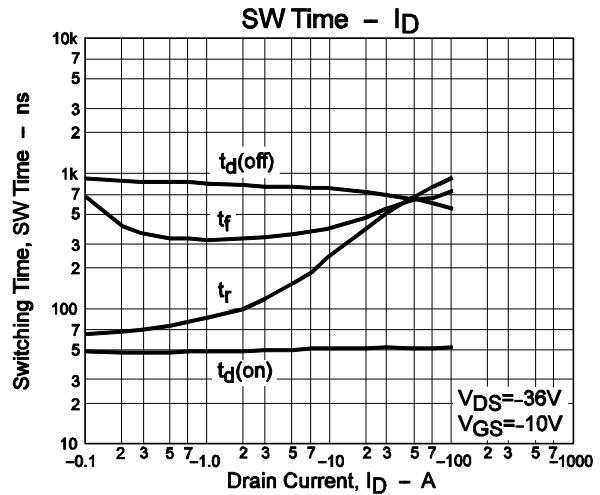


Figure 6. SW Time - I_D

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TYPICAL CHARACTERISTICS

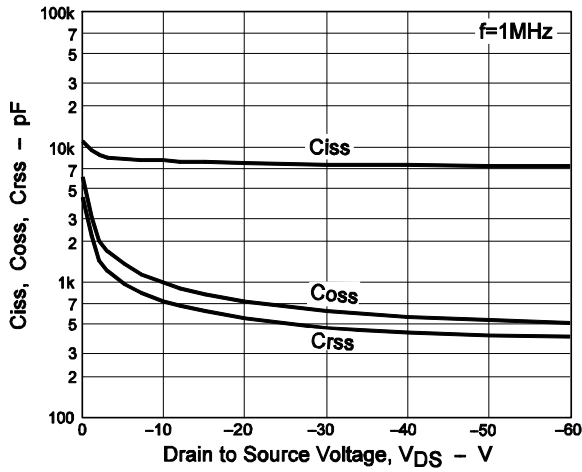


Figure 7. C_{iss} , C_{oss} , C_{rss} - V_{DS}

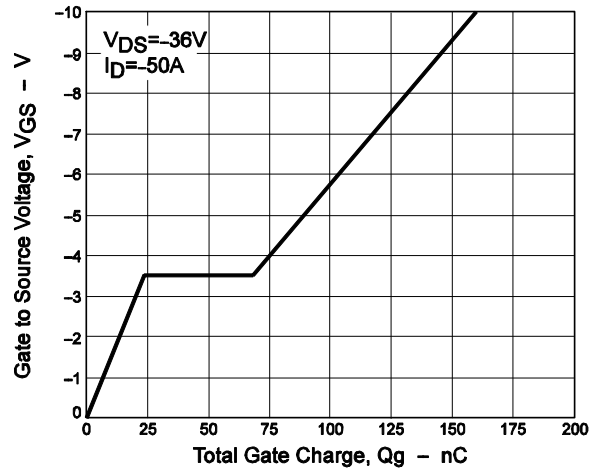


Figure 8. V_{GS} - Q_g

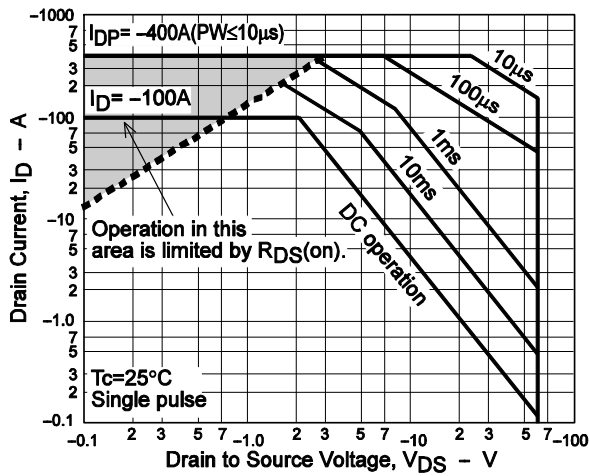


Figure 9. SOA

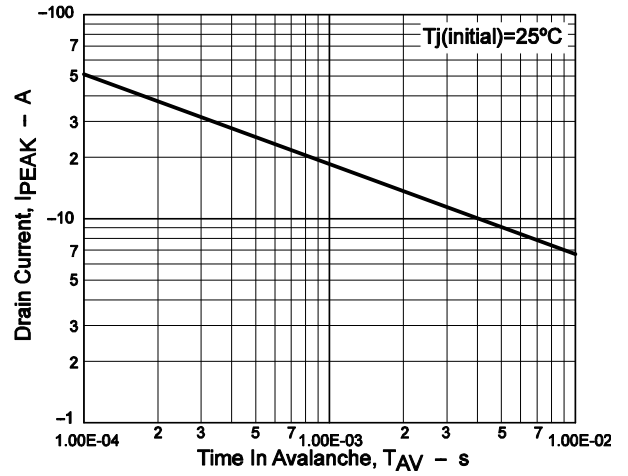


Figure 10. I_{PEAK} - T_{AV}

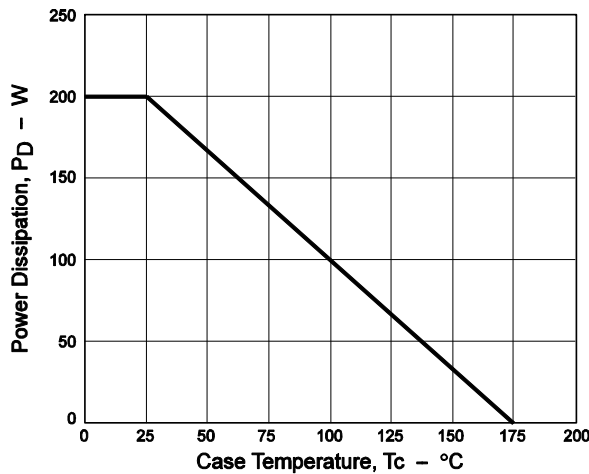


Figure 11. P_D - T_c

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TYPICAL CHARACTERISTICS

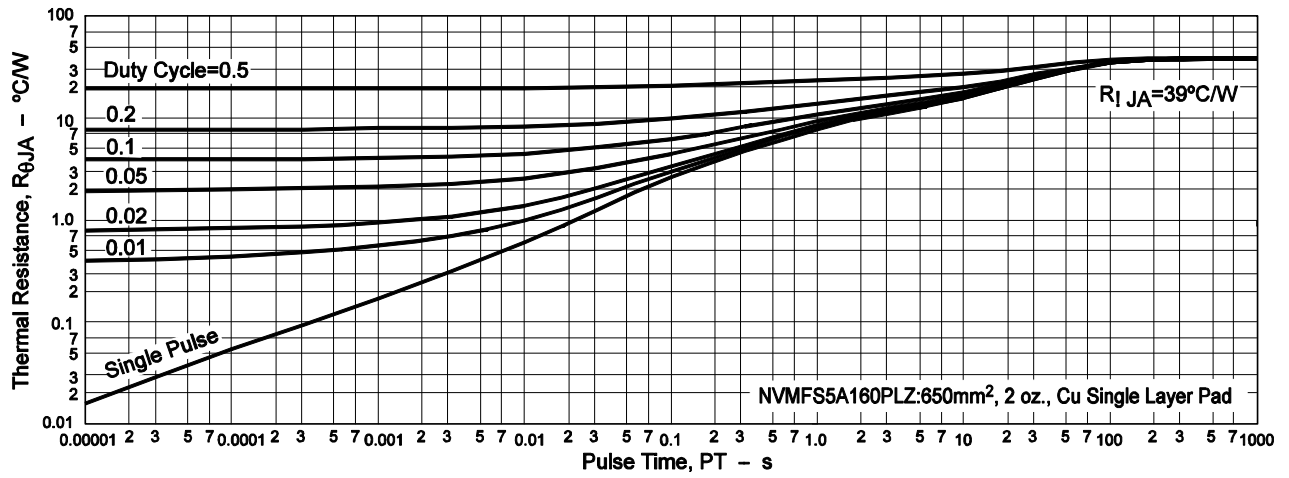


Figure 12. $R_{\theta JA}$ - Pulse Time

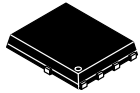
NVMFS5A160PLZ

ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing) [†]
NVMFS5A160PLZT1G	5A160L	DFN5 5x6, 1.27P (SO-8FL) (Pb-Free)	1.500 / Tape & Reel
NVMFS5A160PLZWFT1G	160LWF	DFN5 5x6, 1.27P (SO-8FL) (Pb-Free, Wettable Flanks)	1.500 / Tape & Reel
NVMFS5A160PLZT3G	5A160L	DFN5 5x6, 1.27P (SO-8FL) (Pb-Free)	5.000 / Tape & Reel
NVMFS5A160PLZWFT3G	160LWF	DFN5 5x6, 1.27P (SO-8FL) (Pb-Free, Wettable Flanks)	5.000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

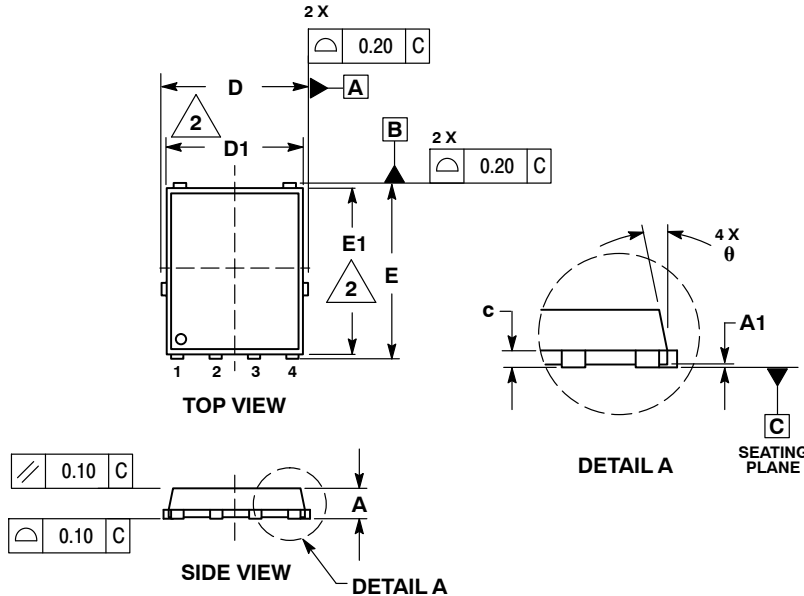
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



1
SCALE 2:1

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018

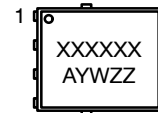


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

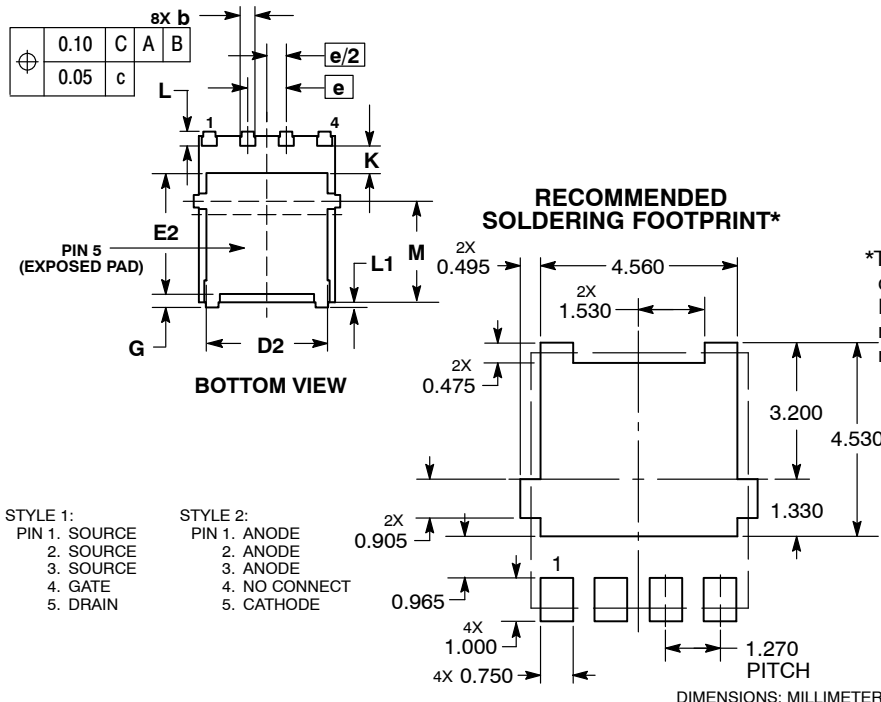
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



- STYLE 1:
1. SOURCE
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN

- STYLE 2:
1. ANODE
 2. ANODE
 3. ANODE
 4. NO CONNECT
 5. CATHODE

DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)	PAGE 1 OF 1

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